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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/665,475	09/22/2003	Tetsuya Taki	T36-160821M/KOH	5511
21254	7590	06/10/2005	EXAMINER	
MCGINN & GIBB, PLLC 8321 OLD COURTHOUSE ROAD SUITE 200 VIENNA, VA 22182-3817			NGUYEN, TUAN H	
			ART UNIT	PAPER NUMBER
			2813	

DATE MAILED: 06/10/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

10/665,475

Applicant(s)

TAKI, TETSUYA

Examiner

Tuan H. Nguyen

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 22 March 2005.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) _____ is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-13, 16, 19 and 20 is/are rejected.
- 7) ☒ Claim(s) 14, 15, 17 and 18 is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
- ☐ Certified copies of the priority documents have been received.
 - ☐ Certified copies of the priority documents have been received in Application No. _____.
 - ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- ☒ Notice of References Cited (PTO-892)
- ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date _____
- ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____
- ☐ Notice of Informal Patent Application (PTO-152)
- ☐ Other: _____

DETAILED ACTION

Claim Objections

Claim 2 is objected to because of the following informalities: In claim 2, last line, "reducing said resistance" should be deleted. Appropriate correction is required.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) and the Intellectual Property and High Technology Technical Amendments Act of 2002 do not apply when the reference is a U.S. patent resulting directly or indirectly from an international application filed before November 29, 2000. Therefore, the prior art date of the reference is determined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).

Claims 1-4, 8-13, 16, 20 are rejected under 35 U.S.C. 102(e) as being anticipated by Hasegawa et al. (US 6,562,129).

See Hasegawa, figs. 1-9 and related text on col. 6-18, particularly figs. 8-9 and text on col. 16-17, Embodiment 7 which discloses the claimed method of producing p-type Group III nitride compound semiconductor including forming a first Group III nitride compound semiconductor layer 36 (see col. 4, last two paragraphs for the material of light guide layer 36) with a p-type dopant (magnesium) concentration of $1 \times 10^{18} \text{ cm}^{-3}$; forming a second Group III nitride compound semiconductor layer 37 with a p-type dopant (magnesium) concentration of $5 \times 10^{17} \text{ cm}^{-3}$ (col. 17, third paragraph); reducing resistance after a beginning of forming the second Group III nitride compound semiconductor layer 37 (col. 18, third paragraph).

With respect to claim 2, fig. 8 and text on col. 17, lines 59-63 shows the step of removing the second Group II nitride compound layer 37 to expose contact layer 31 after reducing resistance by annealing.

With respect to claims 3-4, col. 7, lines 19 shows the thickness of layer 37 of not less than 1 nm.

With respect to claim 9, col. 16, lines 44-50 shows the claimed method comprising n-type Group III nitride doped with silicon.

With respect to claims 10-12, 16, col. 17, lines 24-58 shows the step of furnace heating in hydrogen-free atmosphere at temperature of at least 350°C .

With respect to claim 13, see col. 17, third paragraph for the formation of layers 36 and 37.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 5-7, 19 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hasegawa et al..

See Hasegawa, figs. 1-9 and related text on col. 6-18, particularly figs. 8-9 and text on col. 16-17, Embodiment 7 which discloses the claimed method of producing p-type Group III nitride compound semiconductor as explained above,.

Hasegawa is silent about the diffusing or desorbing of p-type impurities when heating to reduce resistance.

However, it would have been obvious to one having ordinary skill in the art at the time the invention was made to have recognized that since the process is performed under the same conditions, the p-type impurities would inherently diffuse from interstitial sites in the first Group II nitride, or from interstitial sites in the first Group II nitride to the second Group II nitride compound semiconductor layer, or desorbing from the first Group II nitride compound semiconductor layer.

With respect to the thickness of the second Group III nitride layer as claimed in claim 19, it is considered to involve routine optimization while has been held to be within the level of ordinary skill in the art. One of ordinary skill in the requisite art at the time

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the invention was made would have selected a suitable thickness in forming the second Group II layer for obtaining an optimum result.

Allowable Subject Matter

Claims 14-15, 17-18 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The following is a statement of reasons for the indication of allowable subject matter: None of the references of record teaches or suggests the claimed method for producing p-type Group III nitride compound semiconductor layer comprises introducing n-type or n and p-type impurities in the second Group III Nitride layer; or heating the layers in the reaction chamber to thermally decompose the second Group II nitride layer.

Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Tanizawa, and Shin are cited as of interest.

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Response to Arguments

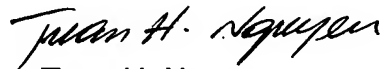
Applicant's arguments with respect to claims 1-20 have been considered but are moot in view of the new ground(s) of rejection.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tuan H. Nguyen whose telephone number is 571-272-1694. The examiner can normally be reached on 9AM-5:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead Jr. can be reached on 571-272-1702. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).



Tuan H. Nguyen
Primary Examiner
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